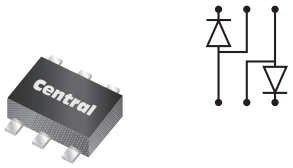
CMLSH05-10DA

SURFACE MOUNT SILICON DUAL, ISOLATED OPPOSING SCHOTTKY DIODE



SOT-563 CASE

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLSH05-10DA consists of two (2) individual electrically isolated 100 Volt Schottky diodes with opposing polarity and packaged in the space saving SOT-563 surface mount case. This device has been designed for size constrained applications requiring high voltage Schottky diodes.

MARKING CODE: 10C

APPLICATIONS:

- LED drive circuits
- DC-DC converter output rectification
- Power management
- Reverse polarity protection

FEATURES:

- Smallest available 100V dual, isolated Schottky diode
- High reverse voltage
- Low forward voltage
- Low reverse leakage current

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Continuous Forward Current	I_F	500	mA
Peak Forward Surge Current, tp=10ms	I_{FSM}	750	mA
Power Dissipation	P_D	250	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	500	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	**TEST CONDITIONS**	**MIN**	**TYP**	**MAX**	**UNITS**
I_R	V_R=100V		0.1	5.0	μA
BV_R	I_R=200μA	100	110		V
V_F	I_F=500mA		0.82	0.85	V

R2 (21-December 2012)

CMLSH05-10DA

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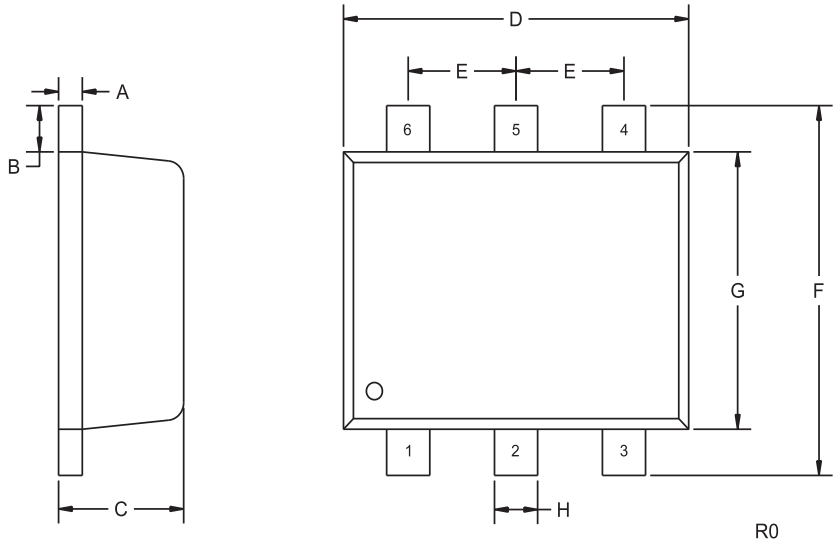
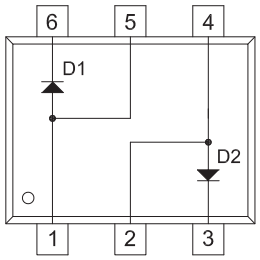
SOT-563 CASE - MECHANICAL OUTLINE



R0

PIN CONFIGURATION



DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

LEAD CODE:
1) Anode D1
2) Anode D2
3) Cathode D2
4) Anode D2
5) Anode D1
6) Cathode D1

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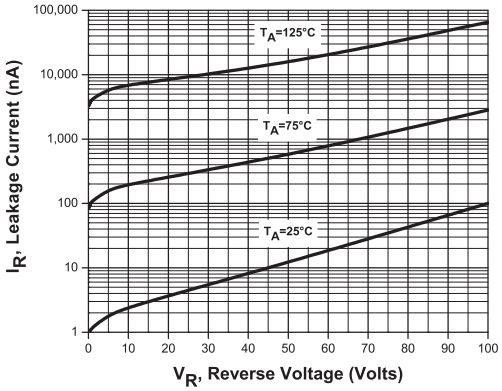
R2 (21-December 2012)

CMLSH05-10DA

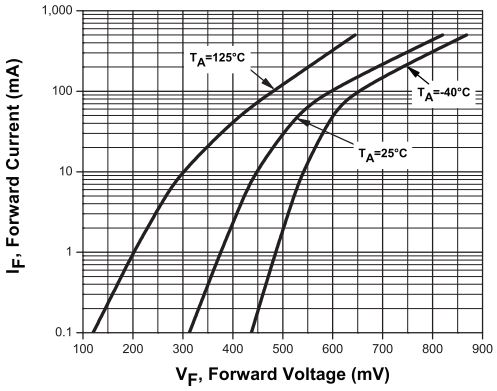
SURFACE MOUNT SILICON DUAL, ISOLATED OPPOSING SCHOTTKY DIODE

TYPICAL ELECTRICAL CHARACTERISTICS

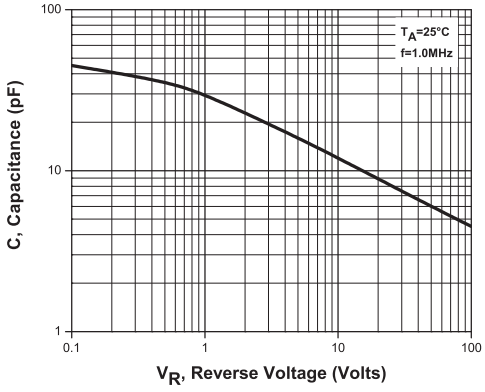
Typical Per Diode Leakage Current



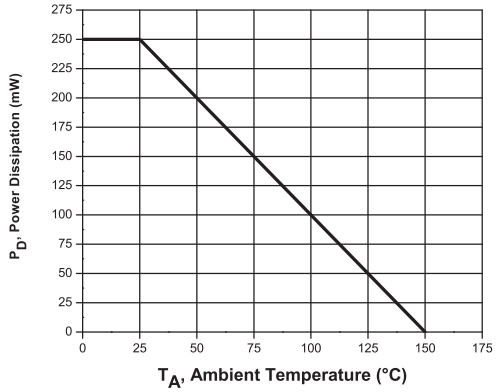
Typical Per Diode Forward Voltage



Typical Per Diode Capacitance



Power Derating



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